

**AMENDMENTS TO THE CLAIMS:**

Please amend claims 1, 3 and 4, as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

**Claim 1 (Currently amended):** A monocrystalline gallium nitride localized substrate, comprising:

a monocrystalline silicon substrate;  
a region of silicon carbide formed ~~on by locally metamorphosing~~ the monocrystalline silicon substrate into silicon carbide; and  
a region of monocrystalline gallium nitride grown on the region of silicon carbide.

**Claim 2 (canceled)**

**Claim 3 (Currently amended):** A monocrystalline gallium nitride localized substrate according to claim 1, further comprising:

a region of silicon nitride formed on the monocrystalline silicon substrate ~~alongside of the region of silicon carbide, the region of silicon nitride positioned other than in said region of monocrystalline gallium nitride.~~

**Claim 4 (Currently amended):** A monocrystalline gallium nitride localized substrate according to claim 1, further comprising:

a region of silicon oxide formed on the monocrystalline silicon substrate ~~alongside of the region of silicon carbide, the region of silicon oxide positioned other than in said region of monocrystalline gallium nitride.~~

**Claim 5 (Previously presented):** A monocrystalline gallium nitride localized substrate according to Claim 1, wherein said monocrystalline silicon substrate is an SOI substrate.

**Claims 6-9 (Canceled).**

**Claim 10 (Previously presented):** A monocrystalline gallium nitride localized substrate according to Claim 3, wherein said monocrystalline silicon substrate is an SOI substrate.

**Claim 11 (Previously presented):** A monocrystalline gallium nitride localized substrate according to Claim 4, wherein said monocrystalline silicon substrate is an SOI substrate.

**Claim 12 (Previously presented):** A monocrystalline gallium nitride localized substrate according to claim 3, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon nitride.

**Claim 13 (Previously presented):** A monocrystalline gallium nitride localized substrate according to claim 4, further comprising:

a region of polycrystalline gallium nitride grown on the region of silicon oxide.